

# DATA SHEET

## **BFG16A**

**NPN 2 GHz wideband transistor**

Product specification  
Supersedes data of November 1992  
File under Discrete Semiconductors, SC14

1995 Sep 12

## NPN 2 GHz wideband transistor

## BFG16A

## FEATURES

- High power gain
- Good thermal stability
- Gold metallization ensures excellent reliability.

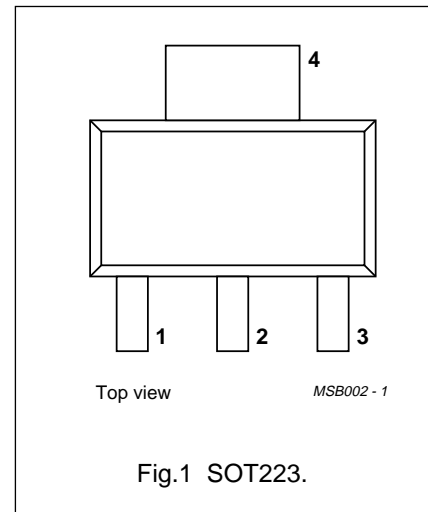
## DESCRIPTION

NPN transistor mounted in a plastic SOT223 envelope.

It is primarily intended for use in wideband amplifiers, aerial amplifiers and vertical amplifiers in high speed oscilloscopes.

## PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	–	25	V
$I_C$	DC collector current		–	–	150	mA
$P_{tot}$	total power dissipation	up to $T_s = 110\text{ °C}$ ; note 1	–	–	1	W
$h_{FE}$	DC current gain	$I_C = 150\text{ mA}$ ; $V_{CE} = 5\text{ V}$ ; $T_j = 25\text{ °C}$	25	80	–	
$f_T$	transition frequency	$I_C = 100\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	1.5	–	GHz
$G_{UM}$	maximum unilateral power gain	$I_C = 100\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	10	–	dB

## Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

## LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	25	V
$V_{EBO}$	emitter-base voltage	open collector	–	2	V
$I_C$	DC collector current		–	150	mA
$P_{tot}$	total power dissipation	up to $T_s = 110\text{ °C}$ ; note 1	–	1	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

## Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

## NPN 2 GHz wideband transistor

BFG16A

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 110\text{ °C}$ ; note 1	40	K/W

## Note

- $T_s$  is the temperature at the soldering point of the collector tab.

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

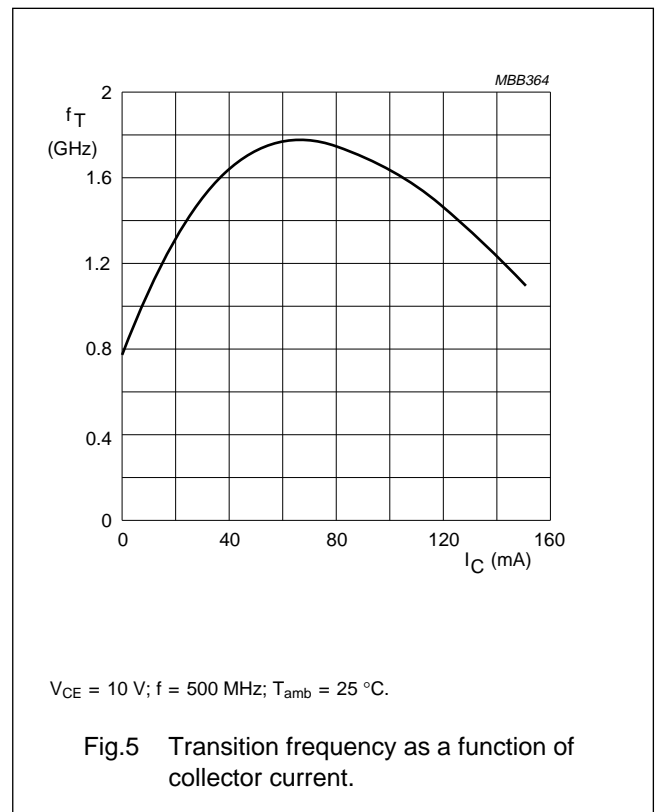
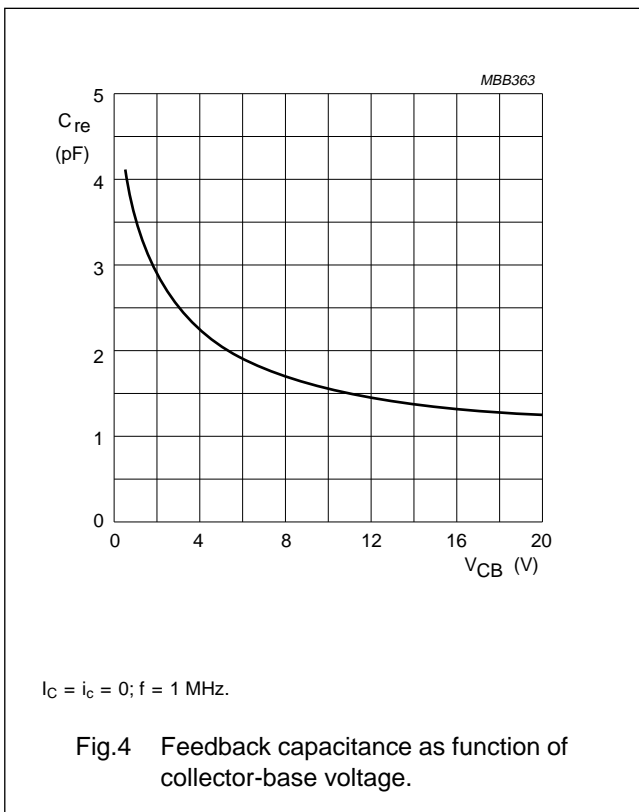
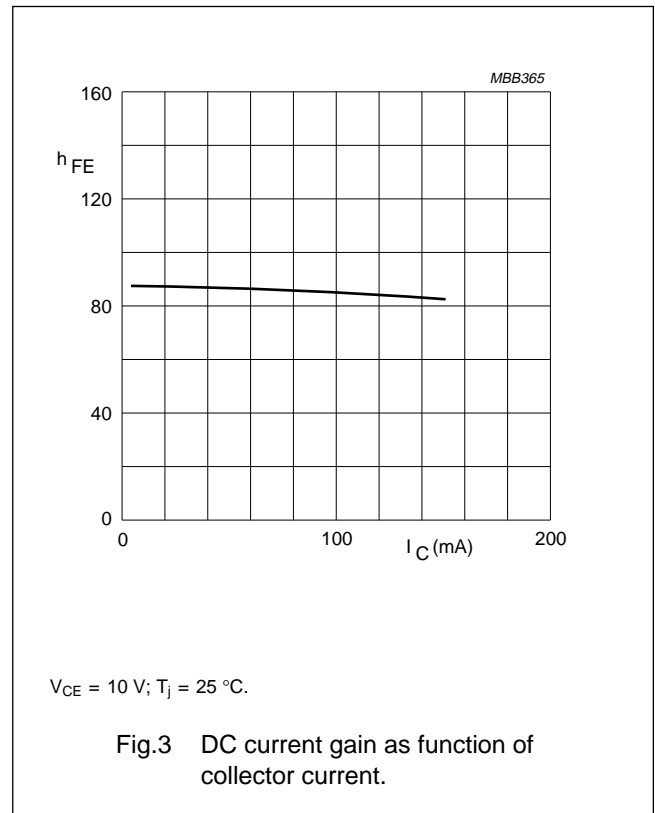
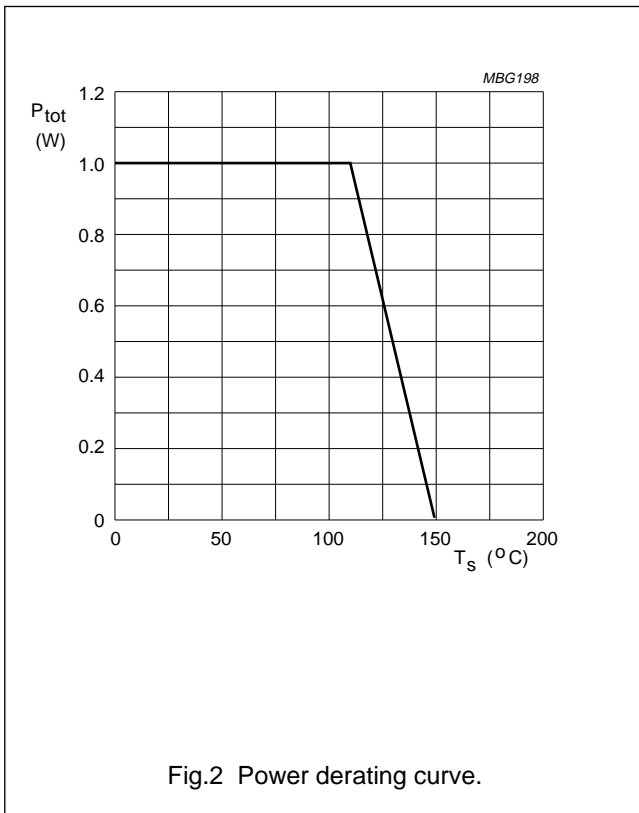
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 0.1\text{ mA}$	25	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 10\text{ mA}$	18	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 0.1\text{ mA}$	3	–	–	V
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = 28\text{ V}$	–	–	20	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_C = 150\text{ mA}$ ; $V_{CE} = 5\text{ V}$	25	80	–	
$C_c$	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	2.5	–	pF
$C_e$	emitter capacitance	$I_C = i_c = 0$ ; $V_{EB} = 0.5\text{ V}$ ; $f = 1\text{ MHz}$	–	10.0	–	pF
$C_{re}$	feedback capacitance	$I_C = 0$ ; $V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	1.5	–	pF
$f_T$	transition frequency	$I_C = 100\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	1.5	–	GHz
$G_{UM}$	maximum unilateral power gain note 1	$I_C = 100\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	10	–	dB

## Note

- $G_{UM}$  is the maximum unilateral power gain, assuming  $s_{12}$  is zero.  $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$  dB.

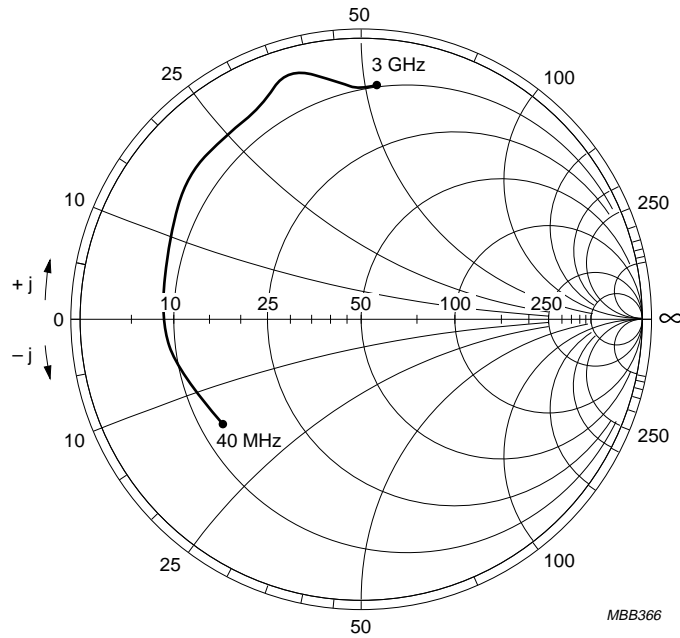
NPN 2 GHz wideband transistor

BFG16A



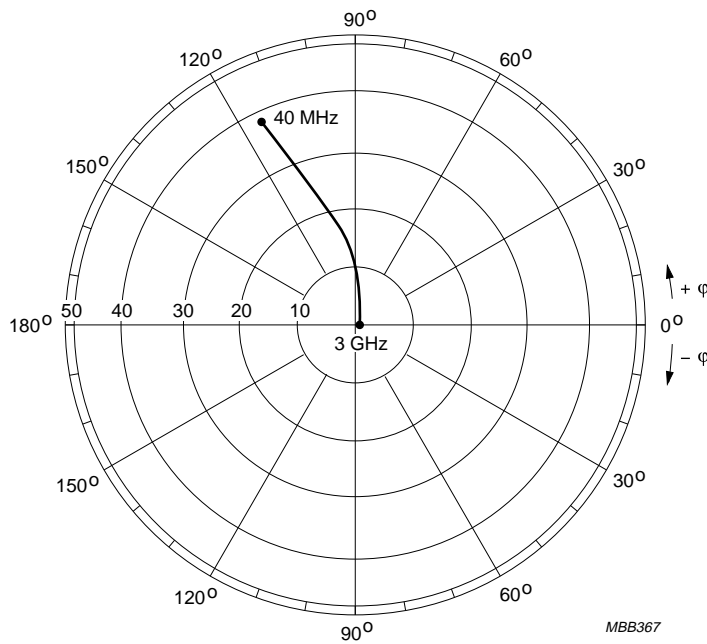
NPN 2 GHz wideband transistor

BFG16A



$I_C = 70 \text{ mA}; V_{CE} = 15 \text{ V}; Z_0 = 50 \Omega.$

Fig.6 Common emitter input reflection coefficient ( $S_{11}$ ).

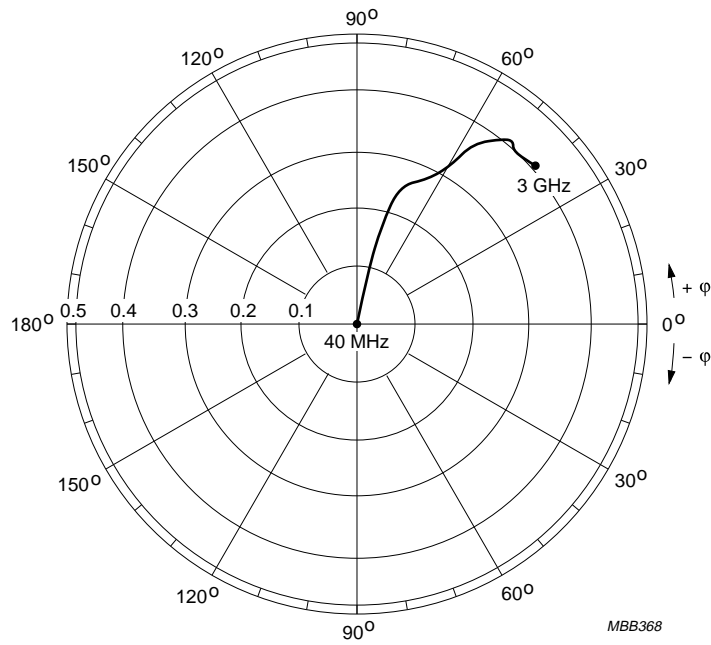


$I_C = 70 \text{ mA}; V_{CE} = 15 \text{ V}.$

Fig.7 Common emitter forward transmission coefficient ( $S_{21}$ ).

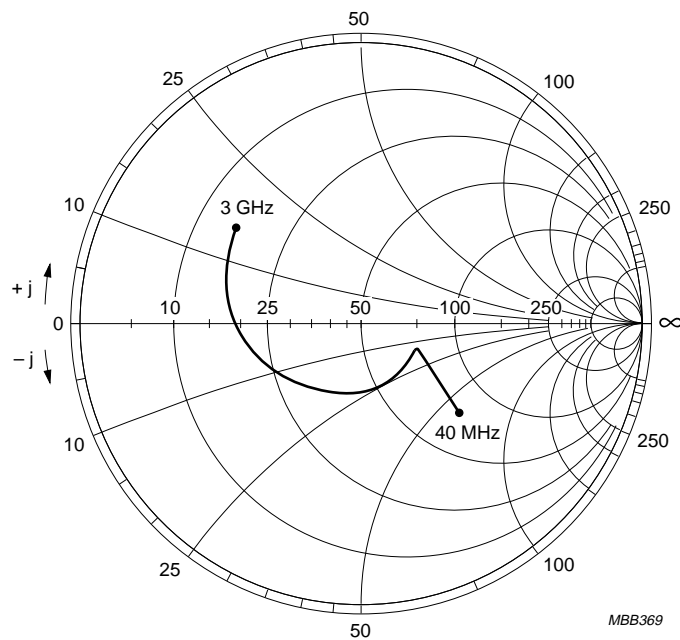
NPN 2 GHz wideband transistor

BFG16A



$I_C = 70 \text{ mA}; V_{CE} = 15 \text{ V}.$

Fig.8 Common emitter reverse transmission coefficient ( $S_{12}$ ).



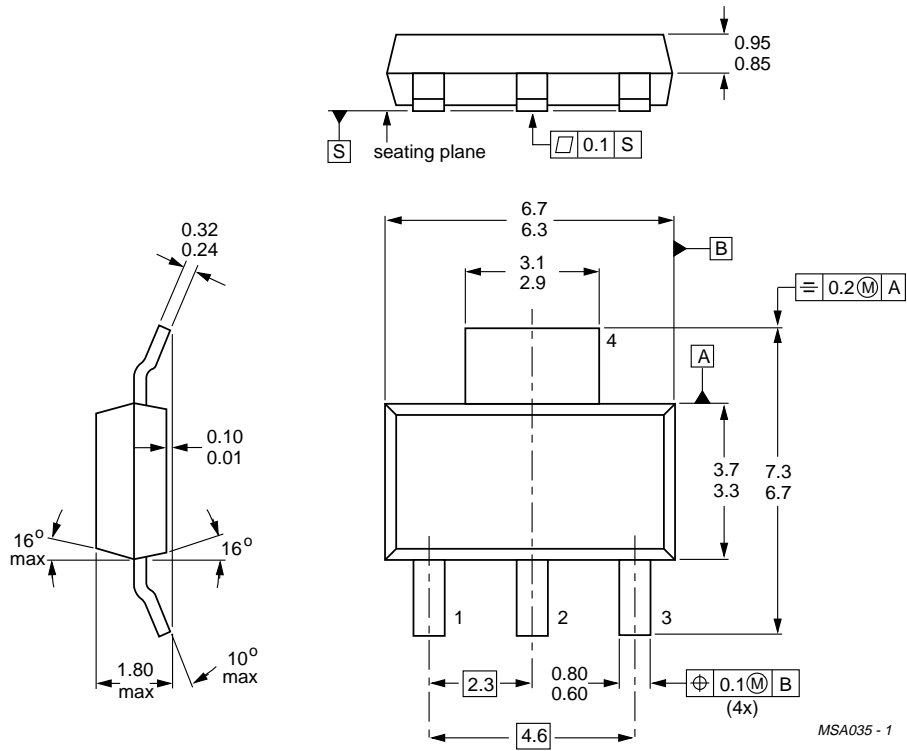
$I_C = 70 \text{ mA}; V_{CE} = 15 \text{ V}; Z_0 = 50 \Omega.$

Fig.9 Common emitter output transmission coefficient ( $S_{22}$ ).

NPN 2 GHz wideband transistor

BFG16A

PACKAGE OUTLINE



Dimensions in mm.

Fig.10 SOT223.

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BFG16A

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Short-form specification	The data in this specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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